



ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748-5089
<http://www.nteinc.com>

NTE5722 Powerblock Module

Features:

- Electrically Isolated Base Plate
- Pressure Contact Technology with Increased Power Cycling Capability
- Space and Weight Savings

Applications:

- AC/DC Motor Drives
- Various Rectifiers
- DC Supply for PWM Inverter

Ratings and Characteristics: ($T_J = +125^\circ\text{C}$ unless otherwise specified)

Maximum Mean On-State Current, $I_{T(\text{AV})}$ ($T_C = +85^\circ\text{C}$, 180°, Half Sine Wave, 50Hz, Single Side Cooled)	90A
Maximum RMS On-State Current, $I_{T(\text{RMS})}$	141A
Maximum Repetitive Peak Off-State Voltage ($V_{\text{DSM}} = 1400\text{V}$, $t_p = 10\text{ms}$), V_{DRM}	1200V
Maximum Repetitive Peak Reverse Voltage ($V_{\text{RSM}} = 1400\text{V}$, $t_p = 10\text{ms}$), V_{RRM}	1200V
Maximum Repetitive Peak Current, I_{DRM} , I_{RRM}	10mA
Maximum Surge On-State Current (10ms Half Sine Wave, $V_R = 720\text{V}$), I_{TSM}	2KA
Maximum I^2t for Fusing Coordination (10ms Half Sine Wave, $V_R = 720\text{V}$), I^2t	$20.4\text{A}^2\text{s} * 10^3$
Maximum Threshold Voltage, V_{TO}	0.8V
On-State Slope Resistance, r_T	$3.01\text{m}\Omega$
Maximum Peak On-State Voltage ($I_{\text{TM}} = 270\text{A}$), $T_J = +25^\circ\text{C}$), V_{TM}	1.7V
Critical Rate of Rise of Off-State Voltage ($V_{\text{DM}} = 804\text{V}$), dv/dt	$800\text{V}/\mu\text{s}$
Critical Rate of Rise of On-State Current, di/dt ($I_{\text{TM}} = 180\text{A}$, Gate Source 1.5A, $t_r \leq 0.5\mu\text{s}$ Repetitive)	$100\text{A}/\mu\text{s}$
RMS Isolation Voltage (50Hz, $t = 1\text{s}$ Min, $I_{\text{ISO}} = 1\text{mA}$ Max), V_{ISO}	2500V
Storage Temperature Range, T_{stg}	-40° to +125°C
Thermal Resistance, Junction-to-Case (Single Side Cooled), R_{thJC}	$0.28^\circ\text{C}/\text{W}$
Thermal Resistance, Case-to-Sink (Single Side Cooled), R_{thCS}	$0.15^\circ\text{C}/\text{W}$
Typical Thermal Connection Torque, F_m	4.0N • m
Typical Mounting Torque, F_m	6.0N • m

Electrical Specifications:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Gate Trigger Current	I _{GT}	V _A = 12V, I _A = 1A, T _J = +25°C	30	-	100	mA
Gate Trigger Voltage	V _{GT}		1.0	-	2.5	V
Holding Current	I _H		20	-	100	mA
Non-Trigger Gate Voltage	V _{GD}	V _{DM} = 804V, T _J = +125°C	0.2	-	-	V

Circuit Diagram

